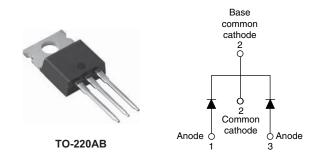
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Ultrafast Rectifier, 16 A FRED Pt®



PRODUCT SUMMARY					
Package	TO-220AB				
I _{F(AV)}	2 x 8 A				
V _R	400 V				
V _F at I _F	0.94 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current

· Material categorization:

• Designed and qualified for industrial level



for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION/APPLICATIONS

FRED Pt[®] series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		400	V			
per leg			8				
Average rectified forward current total device	IF(AV)	$T_{C} = 155 \text{ °C}, \text{ rated } V_{R}$	16	^			
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	100	A			
Peak repetitive forward current	I _{FRM}	T_{C} = 155 °C, rated V_{R} , square wave, 20 kHz	16				
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS PER LEG (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	400	-	-		
F 1 1	M	I _F = 8 A	-	1.19	1.3	V	
Forward voltage	VF	I _F = 8 A, T _J = 150 °C	-	0.94	1.0		
Deverse leekees eurrent		$V_R = V_R$ rated	-	0.2	10		
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	500	μA	
Junction capacitance	CT	V _R = 400 V	-	14	-	pF	
Series inductance	Ls	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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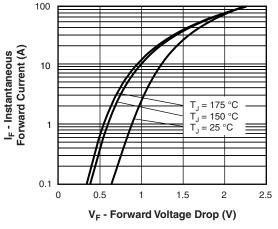
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DYNAMIC RECOVERY CHARACTERISTICS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µA, V _R = 30 V	-	35	60		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	43	-	ns	
		T _J = 125 °C		-	67	-		
Dook rooover / ourrent	1	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/µs V _R = 200 V	-	2.8	-	A	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	6.3	-		
Reverse recovery charge	0	T _J = 25 °C		-	60	-		
	Q _{rr}	T _J = 125 °C		-	210	-	nC	

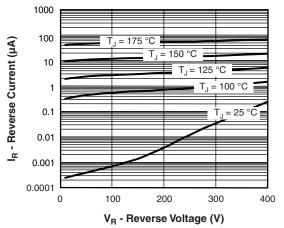
THERMAL MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	e	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance,	per leg	P		-	3.6	4	
junction to case per	device	R _{thJC}		-	1.8	2	
Thermal resistance, junction to ambient		R _{thJA}	Typical socket mount	-	-	50	°C/W
Thermal resistance, case to heatsink		R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight				-	2.0	-	g
weight				-	0.07	-	oz.
Mounting torque				6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device			Case style TO-220AB	16CTU04			

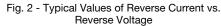
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Fig. 1 - Typical Forward Voltage Drop Characteristics





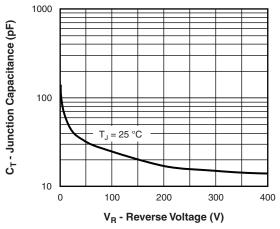


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

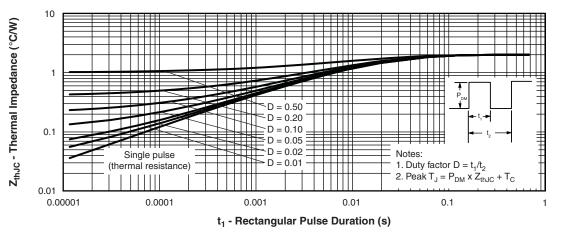
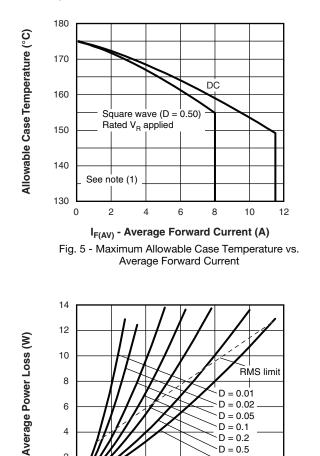


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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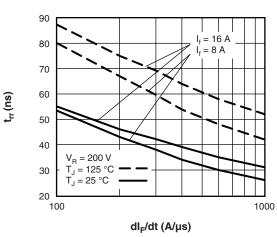
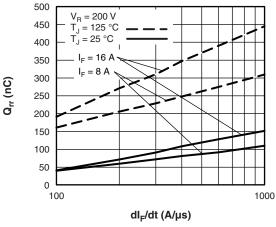


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





Note

8

6

4

2

0

0

2

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

4

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, x \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

6

I_{F(AV)} - Average Forward Current (A)

Fig. 6 - Forward Power Loss Characteristics

D = 0.01

D = 0.02

D = 0.05 D = 0.1

D = 0.2

D = 0.5

10

12

DC

8

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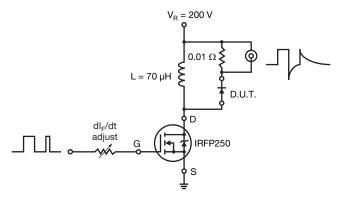


Fig. 9 - Reverse Recovery Parameter Test Circuit

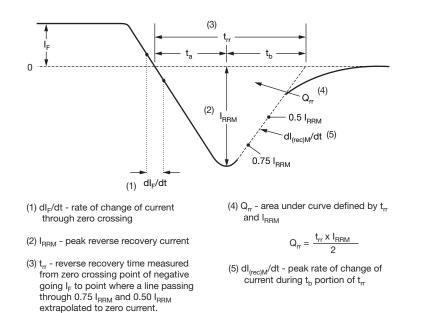
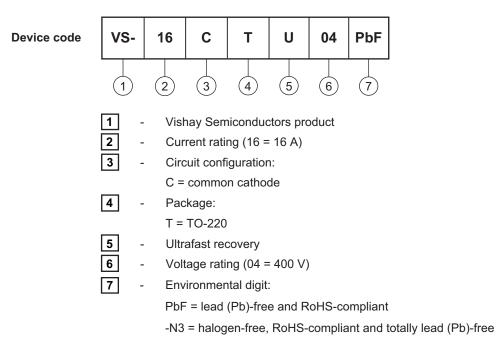


Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-16CTU04PbF	50	1000	Antistatic plastic tube			
VS-16CTU04-N3	50	1000	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
	TO-220ABPbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028			



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TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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